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U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MLT	A1	2002/0100942	08/01/2001	Fitzgerald et al.			06/19/2001
	A2	2002/0084000	07/04/2002	Fitzgerald			12/17/2001
	A3	2002/0096717	07/25/2002	Chu et al.			01/25/2001
	A4	2002/0123197	09/05/2002	Fitzgerald et al.			06/19/2001
	A5	2002/0123183	09/05/2002	Fitzgerald			07/16/2001
	A6	2002/0123167	09/05/2002	Fitzgerald			07/16/2001
	A7	2002/0125497	09/12/2002	Fitzgerald			07/16/2001
	A8	2002/0125471	09/12/2002	Fitzgerald et al.			12/04/2001
	A9	2002/0168864	11/14/2002	Cheng et al.			
	A10	2003/0013323	01/16/2003	Hammond et al.			
	A11	2003/0025131	02/06/2003	Lee et al.			
	A12	2003/0034529	02/20/2003	Fitzgerald et al.			
	A13	2003/0057439	03/17/2003	Fitzgerald			
	A14	2003/0077867	04/24/2003	Fitzgerald			
	A15	2003/0102498	06/05/2003	Braithwaite et al.			
	A16	2003/0227057	12/11/2003	Lochtefeld et al.			10/04/2002
	A17	2004/0005740	01/08/2004	Lochtefeld et al.			06/06/2003
	A18	2004/0031979	02/19/2004	Lochtefeld et al.			06/06/2003
	A19	2004/0075149	04/22/2004	Fitzgerald et al.			07/23/2003
	A20	2004/0219726	11/04/2004	Fitzgerald			05/26/2004
	A21	2004/0262631	12/13/2004	Fitzgerald			04/16/2004
	A22	2005/0009288	01/13/2005	Cheng et al.			03/17/2004
	A23	2005/0156246	07/21/2005	Langdo et al.			03/07/2005
	A24	4,010,045	03/01/1977	Ruehrwein			
	A25	4,710,788	12/01/1987	Dambkes et al.			
	A26	4,900,372	12/13/1990	Lee *et al.*			
	A27	4,987,462	01/22/1991	Kim et al.			
	A28	4,990,979	02/05/1991	Otto			
	A29	4,997,776	03/05/1991	Harame et al.			
	A30	5,013,681	05/07/1991	Godbey et al.			
MLT	A31	5,091,767	02/25/1992	Bean *et al.*			

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U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MLT	A32	5,097,630	03/24/1992	Maeda *et al.*			
	A33	5,155,571	10/13/1992	Wang et al.			
	A34	5,159,413	10/27/1992	Calviello *et al.*			
	A35	5,166,084	11/24/1992	Pfiester			
	A36	5,177,583	01/05/1993	Endo et al.			
	A37	5,202,284	04/01/1993	Kamins et al.			
	A38	5,207,864	05/04/1993	Bhat et al.			
	A39	5,208,182	05/04/1993	Narayan et al.			
	A40	5,210,052	05/11/1993	Takasaki			
	A41	5,212,110	05/18/1993	Pfiester et al.			
	A42	5,221,413	06/22/1993	Brasen et al.			
	A43	5,241,197	08/31/1993	Murakami et al.			
	A44	5,250,445	10/05/1993	Bean et al.			
	A45	5,252,173	10/12/1993	Inoue			
	A46	5,279,687	01/18/1994	Tuppen *et al.*			
	A47	5,285,086	02/08/1994	Fitzgerald, Jr.			
	A48	5,291,439	03/01/1994	Kauffmann, et al.			
	A49	5,298,452	03/29/1994	Meyerson			
	A50	5,308,444	05/03/1994	Fitzgerald *et al.*			
	A51	5,310,451	05/10/1994	Tejwani et al.			
	A52	5,316,958	05/31/1994	Meyerson			
	A53	5,346,848	09/13/1994	Grupen-Shemansky et al.			
	A54	5,374,564	12/20/1994	Bruel			
	A55	5,413,679	05/09/1995	Godbey			
	A56	5,424,243	06/13/1995	Takasaki			
	A57	5,425,846	06/20/1995	Koze *et al.*			
	A58	5,426,069	06/20/1995	Selvakumar et al.			
	A59	5,426,316	06/20/1995	Mohammad			
	A60	5,461,243	10/24/1995	Ek et al.			
	A61	5,461,250	10/24/1995	Burghartz et al.			
MLT	A62	5,462,883	10/31/1995	Dennard et al.			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MLT	A63	5,476,813	12/19/1995	Naruse			
	A64	5,479,033	12/26/1995	Baca et al.			
	A65	5,484,664	01/16/1996	Kitahara et al.			
	A66	5,523,243	06/04/1996	Mohammad			
	A67	5,523,592	06/04/1996	Nakagawa et al.			
	A68	5,534,713	07/09/1996	Ismail et al.			
	A69	5,536,361	07/16/1996	Kondo et al.			
	A70	5,540,785	07/30/1996	Dennard et al.			
	A71	5,596,527	01/12/1997	Tomioka, et al.			
	A72	5,617,351	04/01/1997	Bertin, et al.			
	A73	5,630,905	05/20/1997	Lynch et al.			
	A74	5,633,516	05/27/1997	Mishima *et al.*			
	A75	5,659,187	08/19/1997	Legoues et al.			
	A76	5,683,934	11/04/1997	Candelaria			
	A77	5,698,869	12/16/1997	Yoshimi et al.			
	A78	5,714,777	02/03/1998	Ismail et al.			
	A79	5,728,623	03/17/1998	Mori			
	A80	5,739,567	04/14/1998	Wong			
	A81	5,759,898	06/02/1998	Ek et al.			
	A82	5,777,347	07/07/1998	Bartelink			
	A83	5,786,612	07/28/1998	Otani et al.			
	A84	5,786,614	07/28/1998	Chuang, et al.			
	A85	5,792,679	08/11/1998	Nakato			
	A86	5,801,085	09/01/1998	Kim *et al.*			
	A87	5,808,344	09/15/1998	Ismail et al.			
	A88	5,810,924	09/22/1998	Legoues *et al.*			
	A89	5,828,114	10/27/1998	Kim *et al.*			
	A90	5,847,419	12/08/1998	Imai et al.			
	A91	5,859,864	01/12/1999	Jewell			
	A92	5,877,070	03/02/1999	Goesele et al.			
MLT	A93	5,891,769	04/06/1999	Liaw et al.			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MLT	A94	5,906,708	05/25/1999	Robinson et al.			
	A95	5,906,951	05/25/1999	Chu et al.			
	A96	5,912,479	06/15/1999	Mori et al.			
	A97	5,943,560	08/24/1999	Chang et al.			
	A98	5,963,817	10/05/1999	Chu et al.			
	A99	5,966,622	10/12/1999	Levine et al.			
	A100	5,998,807	12/07/1999	Lustig et al.			
	A101	6,010,937	01/04/2000	Karam *et al.*			
	A102	6,013,134	01/11/2000	Chu et al.			
	A103	6,030,884	02/29/2000	Mori			
	A104	6,033,974	03/07/2000	Henley et al.			
	A105	6,033,995	03/07/2000	Muller			
	A106	6,039,803	03/21/2000	Fitzgerald *et al.*			
	A107	6,058,044	05/02/2000	Sugiura et al.			
	A108	6,059,895	05/09/2000	Chu et al.			
	A109	6,074,919	06/13/2000	Gardner et al.			
	A110	6,096,590	08/01/2000	Chan et al.			
	A111	6,103,559	08/15/2000	Gardner et al.			
	A112	6,107,653	08/22/2000	Fitzgerald			
	A113	6,111,267	08/29/2000	Fischer et al.			
	A114	6,117,750	09/12/2000	Bensahel et al.			
	A115	6,124,614	09/26/2000	Ryum *et al.*			
	A116	6,130,453	10/10/2000	Mei, et al.			
	A117	6,133,799	10/17/2000	Favors, Jr., et al.			
	A118	6,140,687	10/31/2000	Shimomura et al.			
	A119	6,143,636	11/07/2000	Forbes, et al.			
	A120	6,153,495	11/28/2000	Kub et al.			
	A121	6,154,475	11/28/2000	Soref et al.			
	A122	6,160,303	12/12/2000	Fattaruso			
	A123	6,162,688	12/19/2000	Gardner et al.			
MLT	A124	6,184,111	02/06/2001	Henley et al.			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MLT	A125	6,191,006	02/20/2001	Mori			
	A126	6,191,007	02/20/2001	Matsui et al.			
	A127	6,191,432	02/20/2001	Sugiyama et al.			
	A128	6,194,722	02/27/2001	Fiorini et al.			
	A129	6,204,529	03/20/2001	Lung, et al.			
	A130	6,207,977	03/01/2001	Augusto			
	A131	6,210,988	04/03/2001	Howe et al.			
	A132	6,218,677	04/17/2001	Broekaert			
	A133	6,232,138	05/15/2001	Fitzgerald et al.			
	A134	6,235,567	05/22/2001	Huang			
	A135	6,242,324	06/05/2001	Kub et al.			
	A136	6,249,022	06/19/2001	Lin, et al.			
	A137	6,251,755	06/26/2001	Furukawa et al.			
	A138	6,261,929	07/01/2001	Gehrke et al.			
	A139	6,271,551	08/07/2001	Schmitz et al.			
	A140	6,271,726	08/07/2001	Fransis et al.			
	A141	6,291,321	09/18/2001	Fitzgerald			
	A142	6,313,016	11/06/2001	Kibbel et al.			
	A143	6,316,301	11/13/2001	Kant			
	A144	6,323,108	11/27/2001	Kub et al.			
	A145	6,329,063	12/11/2001	Lo et al.			
	A146	6,335,546	01/01/2002	Tsuda et al.			07/30/1999
	A147	6,350,993	02/26/2002	Chu et al.			
	A148	6,368,733	04/09/2002	Nishinaga			08/05/1999
	A149	6,372,356	04/16/2002	Thornton et al.			04/028/2000
	A150	6,399,970	06/04/2002	Kubo et al.			09/16/1997
	A151	6,403,975	06/11/2002	Brunner et al.			
	A152	6,406,589	06/18/2002	Yanagisawa			
	A153	6,407,406	06/18/2002	Tezuka			06/29/1999
	A154	6,425,951	07/30/2002	Chu et al.			08/06/1999
MLT	A155	6,429,061	08/06/2002	Rim			07/26/2000

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MLT	A156	6,521,041	02/18/2003	Wu et al.			04/09/1999
	A157	6,521,041	02/18/2003	Wu et al.			04/09/1999
	A158	6,555,839	04/29/2003	Fitzgerald			05/16/2001
	A159	6,573,126	06/03/2003	Cheng et al.			08/10/2001
	A160	6,583,015	06/24/2003	Fitzgerald et al.			08/06/2001
	A161	6,593,191	07/15/2003	Fitzgerald			05/16/2001
	A162	6,602,613	08/05/2003	Fitzgerald			
	A163	6,646,322	11/11/2003	Fitzgerald			07/16/2001
	A164	6,649,480	11/18/2003	Fitzgerald et al.			06/19/2001
	A165	6,677,192	01/13/2004	Fitzgerald			07/16/2001
	A166	6,703,144	03/09/2004	Fitzgerald			03/18/2003
	A167	6,703,688	03/09/2004	Fitzgerald			07/16/2001
	A168	6,723,661	04/20/2004	Fitzgerald			07/16/2001
	A169	6,724,008	04/20/2004	Fitzgerald			07/16/2001
	A170	6,730,551	05/04/2004	Lee et al.			08/02/2002
	A171	6,750,130	06/15/2004	Fitzgerald			01/07/2001
	A172	6,830,976	12/14/2004	Fitzgerald			07/16/2001
	A173	6,876,010	04/05/2005	Fitzgerald			06/07/2000
MLT	A174	6,881,632	04/19/2005	Fitzgerald et al.			07/01/2000

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FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
MLT	B1	2001-319935	11/16/2001	JP				N	Y
	B2	4-307974	10/30/1992	JP				N	N
	B3	10-270685	10/09/1998	JP				N	Y
	B4	6-252046	11/19/1992	JP				N	Y
	B5	7-240372	09/12/1995	JP				NO	Abstract
	B6	11-233744	08/27/1999	JP				N	N
	B7	2-210816	08/22/1990	JP				N	Abstract
	B8	6-177046	06/24/1994	JP				N	Abstract
	B9	5-166724	07/02/1993	JP				N	Abstract
	B10	61-141116	06/28/1996	JP				N	Abstract
	B11	7-106446	04/21/1995	JP				N	N
	B12	3-36717	02/18/1991	JP				N	Abstract
	B13	2000-031491	01/28/2000	JP				N	N
	B14	2000-021783	08/31/2000	JP				N	Y
	B15	00/48239	08/17/2000	WO				N	Y
	B16	00/54338	09/14/2000	WO				N	Y
	B17	98/59365	12/30/1998	WO				N	Y
	B18	99/53539	10/21/1999	WO				N	Y
	B19	41 01 167	07/23/1992	DE				N	N
	B20	1 020 900	07/19/2000	EP				N	Y
	B21	1 174 928	01/23/2002	EP				N	Y
	B22	0 587 520	03/16/1994	EP				N	Y
	B23	2 342 777	04/19/2000	GB				Y	Y
	B24	0 828 296	03/11/1998	EP				N	Y
	B25	0 683 522	11/22/1995	EP				N	Y
	B26	0 838 858	04/29/1998	EP				N	N
	B27	0 829 908	03/18/1998	EP				N	Y
	B28	63-73398	04/02/1988	JP				N	N
	B29	6-244112	09/02/1994	JP				N	N
MLT	B30	7-094420	04/07/1995	JP				N	Abstract

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OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.		OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)
MLT	C1	Armstrong et al., "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," IEDM Technical Digest (1995 International Electron Devices Meeting) pp. 761-764.
	C2	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices", PhD Thesis, Massachusetts Institute of Technology, 1999, pp. 1-154.
	C3	Augusto et al., "Proposal for a New Process Flow for the Fabrication of Silicon-based Complementary MOD-MOSFETs without ion Implantation," Thin Solid Films, vol. 294, no. 1-2, pp. 254-258 (February 15, 1997).
	C4	Borenstein et al., "A New Ultra-Hard Etch-Stop Layer for High Precision Micromachining," Proceedings of the 1999 12th IEEE International Conference on Micro Electro Mechanical Systems (MEMs) (January 17-21, 1999) pp. 205-210.
	C5	Bouillon et al., "Search for the optimal channel architecture for 0.18/0.12 μm bulk CMOS Experimental study," IEEE, (1996) pp. 21.2.1-21.2.4.
	C6	Bruel et al., "®SMART CUT: A Promising New SOI Material Technology," Proceedings 1995 IEEE International SOI Conference (October 1995) pp. 178-179.
	C7	Bruel, "Silicon on Insulator Material Technology," Electronic Letters, Vol. 13, No. 14 (July 6, 1995) pp. 1201-1202.
	C8	Bufler et al., "Hole transport in strained Si1-xGex alloys on Si1-yGey substrates," Journal of Applied Physics, Vol. 84, No. 10 (November 15, 1998) pp. 5597-5602.
	C9	Bulsara et al., "Relaxed $In_xGa_{1-x}As$ Graded Buffers Grown with Organometallic Vapor Phase Epitaxy on GaAs," Applied Physics Letters, Vol. 72, Issue 13 (July 30, 1998), pp. 1608-1610.
	C10	Bulsara, "Materials Issues with the Integration of Lattice-Mismatched $In_xGa_{1-x}As$ on GaAs," PhD Thesis, MIT, June 1998, pp. 1-178.
	C11	Burghartz et al., "Microwave Inductors and Capacitors in Standard Multilevel Interconnect Silicon Technology", IEEE Transactions on Microwave Theory and Techniques, Vol. 44, No. 1, January 1996, pp. 100-104.
	C12	Carlin et al., "High Efficiency GaAs-on-Si Solar Cells with High Voc Using Graded GeSi Buffers," IEEE (2000) pp. 1006-1011
	C13	Chang et al., "Selective Etching of SiGe/Si Heterostructures," Journal of the Electrochemical Society, No. 1 (January 1991) pp. 202-204.
	C14	Charasse et al., "MBE Growth of GaAs on Si at Thomson," Institute of Electronic Structure and Laser
	C15	Crumbaker et al., "The Influence of Dislocation Density on Electron Mobility in InP Films on Si," Applied Physics Letters, Vol. 59, Issue 9 (08/26/91), pp. 1090-1092.
MLT	C16	Cullis et al, "Growth ripples upon strained SiGe epitaxial layers on Si and misfit dislocation interactions," Journal of Vacuum Science and Technology A, Vol. 12, No. 4 (July/August 1994) pp. 1924-1931.

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OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.		OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)
MLT	C17	Currie et al. "Controlling Threading Dislocation in Ge on Si Using Graded SiGe Layers and Chemical-Mechanical Polishing" vol. 72 No. 14 (Feb. 1998) pp. 1718-1720.
	C18	Dilliway et al., "Characterization of Morphology and Defects in Silicon Germanium Virtual Substrates," Journal of Materials Science, Vol. 11, Issue 7 (2000), pp. 549-556.
	C19	Eaglesham et al., "Dislocation-Free Stranski-Krastanow Growth of Ge on Si(100)," Physical Review Letters, Vol. 64, No. 16 (April 16, 1990) pp. 1943-1946.
	C20	Erdtmann et al., "Gainas/Inp Quantum Well Infrared Photodetectors on Si Substrate for Low-Cost Focal Plan Arrays," PhD Thesis, Northwestern University, 2000, pp. 1-225.
	C21	Feijoo et al., "Epitaxial Si-Ge Etch Stop Layers with Ethylene Diamine Pyrocatechol for Bonded and Etchback Silicon-on-Insulator," Journal of Electronic Materials, Vol. 23, No. 6 (June 1994) pp. 493-496.
	C22	Fischetti et al., "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys," J. Appl. Phys., Vol. 80, No. 4 (August 15, 1996) pp. 2234-2252.
	C23	Fitzgerald et al., "Dislocation dynamics in relaxed graded composition semiconductors," Materials Science and Engineering B67, (1999) pp. 53-61.
	C24	Fitzgerald et al., "GeSi/Si Nanostructures," Department of Material Science, MIT (1995), pp 1-15.
	C25	Fitzgerald et al., "Relaxed GexSi1-x structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," AT&T Bell Laboratories, Murray Hill, NJ 07974 (1992) American Vacuum Society, pp. 1807-1819
	C26	Fitzgerald et al., "Totally Relaxed GexSi1-x Layers with Low Threading Dislocation Densities Grown on Si Substrates," Applied Physics Letters, Vol. 59, No. 7 (August 12, 1991) pp. 811-813.
	C27	Garone et al., "Silicon vapor phase epitaxial growth catalysis by the presence of germane," Applied Physics Letters, Vol. 56, No. 13 (March 26, 1990) pp. 1275-1277.
	C28	Giovane et al., "Strain-Balanced Silicon-Germanium Materials for Near IR Photodetection in Silicon-Based Optical Interconnects," PhD Thesis, MIT, 1998, pp. 1-134.
	C29	Gray and Meyer, "Analysis and Design of Analog Integrated Circuits", John Wiley & Sons, 1984, pp. 605-632.
	C30	Grillot et al., "Acceptor diffusion and segregation in (AlxGa1-x)0.5In0.5P heterostructures, Vol. 91, No. 8 (April 15, 2002), pps. 4891-4899.
	C31	Grützmacher et al., "Ge segregation in SiGe/Si heterostructures and its dependence on deposition technique and growth atmosphere," Applied Physics Letters, Vol. 63, No. 18 (November 1, 1993) pp. 2531-2533.
	C32	Hackbarth et al., "Alternatives to thick MBE-grown relaxed SiGe buffers," Thin Solid Films, Vol. 369, No. 1-2 (July 2000) pp. 148-151.
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